



1SV298

Silicon Epitaxial PIN Diode

π Type Attenuator Applications

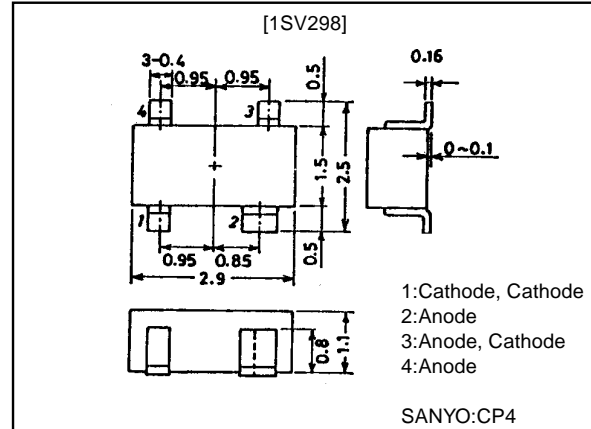
Features

- Composite type with 3 diodes contained in the CP package currently in use, improving the mounting efficiency greatly.
- Small interterminal capacitance ($C=0.23\text{pF}$ typ).
- Small forward series resistance ($r_s=7.5\Omega$ typ).

Package Dimensions

unit:mm

1269



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|-----------|------------|-------------|------------------|
| Reverse Voltage | V_R | | 50 | V |
| Forward Current | I_F | | 50 | mA |
| Allowable Power Dissipation | P | | 150 | mW |
| Junction Temperature | T_j | | 125 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | | -55 to +125 | $^\circ\text{C}$ |

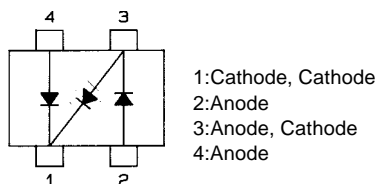
Electrical Characteristics at $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------|--------|--------------------------------------|---------|-------|------|---------------|
| | | | min | typ | max | |
| Reverse Voltage | V_R | $I_R=10\mu\text{A}$ | 50 | | | V |
| Reverse Current | I_R | $V_R=50\text{V}$ | | | 0.1 | μA |
| Forward Voltage | V_F | $I_F=50\text{mA}$ | | 0.975 | 1.15 | V |
| Interterminal Capacitance | C | $V_R=50\text{V}, f=1\text{MHz}$ | | 0.23 | | pF |
| Series Resistance | rs | $I_F=10\mu\text{A}, f=100\text{MHz}$ | | 2400 | | Ω |
| | | $I_F=10\text{mA}, f=100\text{MHz}$ | 6.5 | 7.5 | 10.0 | Ω |

Note : The specifications shown above are for each individual diode.

· Marking:QV

Electrical Connection

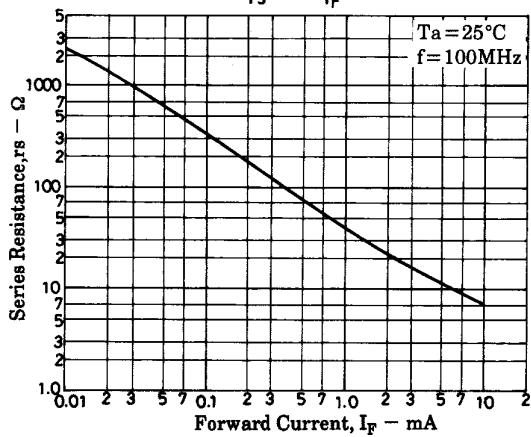
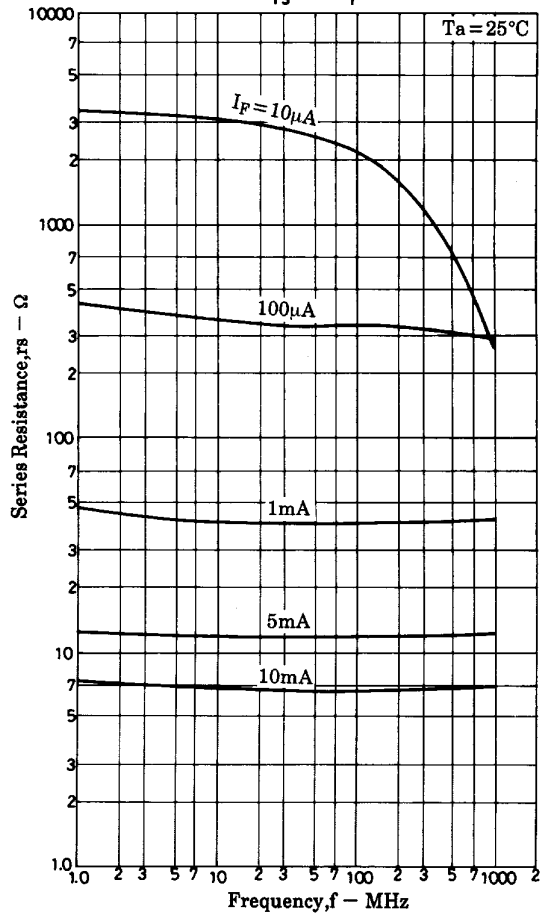
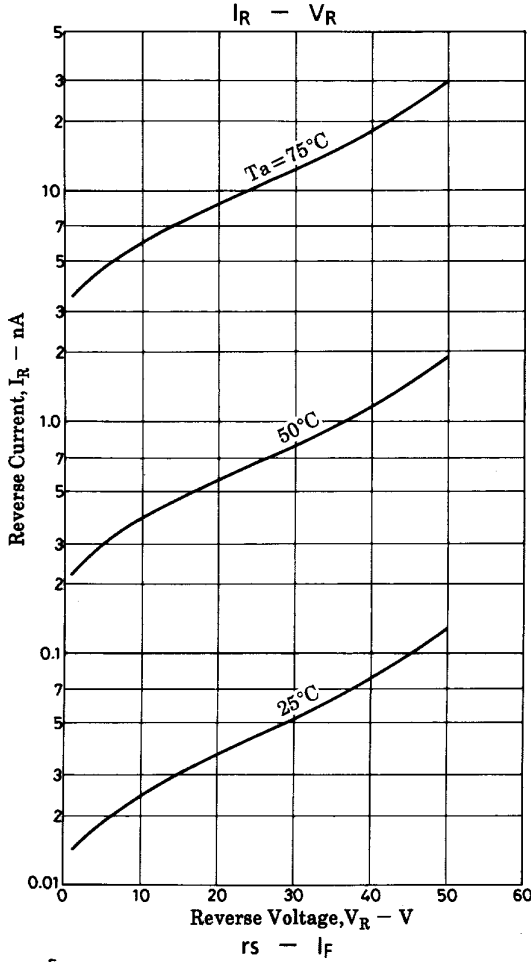
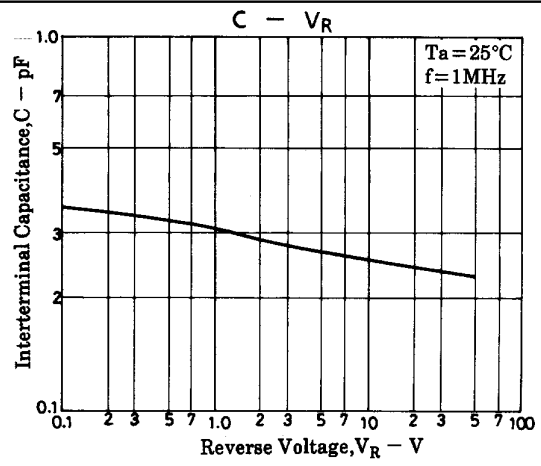
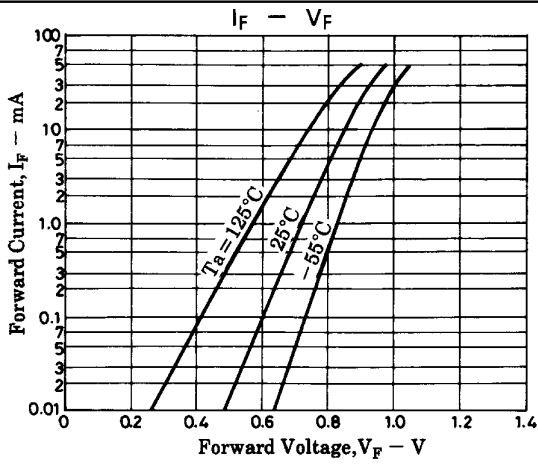


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